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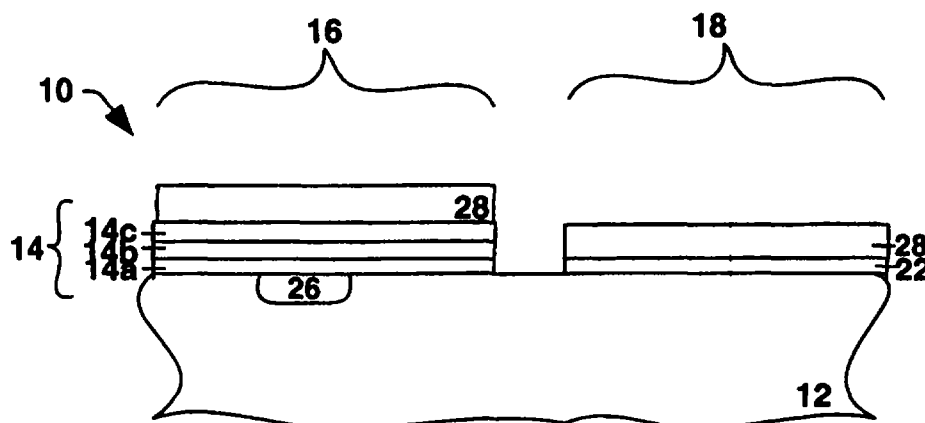
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(54) Title: SIMULTANEOUS FORMATION OF CHARGE STORAGE AND BITLINE TO WORLDLINE ISOLATION



(57) Abstract: One aspect of the present invention relates to a method of forming a non-volatile semiconductor memory device, involving the sequential or non-sequential steps of forming a charge trapping dielectric (14) over a substrate (12), the substrate (12) having a core region (16) and a periphery region (18), removing at least a portion of the charge trapping dielectric (14) in the periphery region (18), forming a gate dielectric (22) in the periphery region (18), forming buried bitlines (26) in the core region (16), and forming gates (28) in the core region (16) and the periphery region (18)

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